2N5629 2N5630 NPN
2N6029 2N6030 PNP

COMPLEMENTARY SILICON POWER TRANSISTORS

TO-3 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5629, 2N6029 series devices are complementary silicon power transistors, manufactured by the epitaxial base process, designed for high voltage and high power amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C)	**SYMBOL**	**2N5629 2N6029**	**2N5630 2N6030**	**UNITS**
Collector-Base Voltage	V_{CBO}	100	120	V
Collector-Emitter Voltage	V_{CEO}	100	120	V
Emitter-Base Voltage	V_{EBO}	7.0		V
Continuous Collector Current	I_C	16		A
Peak Collector Current	I_{CM}	20		A
Continuous Base Current	I_B	5.0		A
Power Dissipation	P_D	200		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		°C
Thermal Resistance	Θ_{JC}	0.875		°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

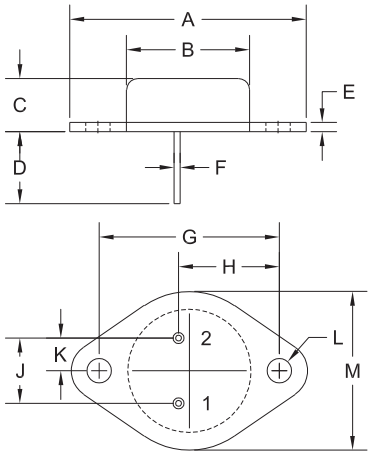
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=Rated V_{CBO}		1.0	mA
I_{CEX}	V_{CE}=Rated V_{CEO}, V_{EB}=1.5V		1.0	mA
I_{CEX}	V_{CE}=Rated V_{CEO}, V_{EB}=1.5V, T_C=150°C		5.0	mA
I_{CEO}	V_{CE}=½Rated V_{CEO}		1.0	mA
I_{EBO}	V_{EB}=7.0V		1.0	mA
BV_{CEO}	I_C=200mA (2N5629, 2N6029)	100		V
BV_{CEO}	I_C=200mA (2N5630, 2N6030)	120		V
$V_{CE(SAT)}$	I_C=10A, I_B=1.0A		1.0	V
$V_{CE(SAT)}$	I_C=16A, I_B=4.0A		2.0	V
$V_{BE(SAT)}$	I_C=10A, I_B=1.0A		1.8	V
$V_{BE(ON)}$	V_{CE}=2.0V, I_C=8.0A		1.5	V
h_{FE}	V_{CE}=2.0V, I_C=8.0A (2N5629, 2N6029)	25	100	
h_{FE}	V_{CE}=2.0V, I_C=8.0A (2N5630, 2N6030)	20	80	
h_{FE}	V_{CE}=2.0V, I_C=16A	4.0		
h_{fe}	V_{CE}=10V, I_C=4.0A, f=1.0kHz	15		
f_T	V_{CE}=20V, I_C=1.0A, f=500kHz	1.0		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=100kHz (NPN)		500	pF
C_{ob}	V_{CB}=10V, I_E=0, f=100kHz (PNP)		1.0	nF

R1 (19-March 2014)

2N5629 2N5630 NPN
2N6029 2N6030 PNP

COMPLEMENTARY SILICON POWER TRANSISTORS

TO-3 CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:
1) Base
2) Emitter
Case) Collector

MARKING:
FULL PART NUMBER

R1 (19-March 2014)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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